Instanton in Disordered Peierls Systems

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W e study disordered Peierls systems described by the Fluctuating Gap

M odel. We show that the typical electron states with energies lying deep

inside the pseudogap are localized near large disorder uctuations (instan-

tons), which have the form of a soliton-antisoliton pair. Using the \saddle-

point" method we obtain the average density of states and the average

optical absorption coe cient at small energy.

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D isorder in quasi-one-dim ensional conductors strongly a ects the electron states, re-

ducing the tendency of these m aterials to develop $2k_F$ -instabilities, such as the Peierls

instability. Existing Peierls materials, like the conjugated polymer trans-polyacetylene,

are known to su er from various kinds of disorder: conform ational defects, cross-links,

im purities, etc. While in a perfect Peierls chain the single-electron spectrum has a gap,

with a value related to the amplitude of the periodic chain distortion, in a disordered

chain the gap is led. At weak disorder, the density of disorder-induced states that occur

inside the gap is small, leading to a pseudogap, while at large disorder the gap disappears

entirely and in the middle of the band the density may even diverge.

In this Letter, we not the typical form of the disorder-induced electron states lying

close to the center of the pseudogap. In addition to giving new insight into these disor-

dered systems, this result is useful, as it allows for a relatively easy calculation of disorder

averages. As examples, we will explicitly calculate the average density of states and the

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average absorption coe cient at small energies.

It is crucial for our approach, that a large disorder uctuation is required to create an electron state close to the center of the pseudogap, in plying that the probability for such a state to occur is small at weak disorder. The main contribution to the density of states at small energy then comes from the disorder realizations close to one most probable uctuation. The form of this uctuation can be found consistently with the form of the wave function of the electron state induced inside the pseudogap. This wave function turns out to be localized in the vicinity of the disorder uctuation. A similar situation is encountered when calculating the density of states of electrons moving in a random potential at large negative energies. These states were found to be localized in regions where the disorder potential has the form of a deep well.

The approximate calculation of disorder averages, valid when the dominant contribution comes from a small part of all possible disorder realizations, is closely related to the semiclassical approximation in quantum mechanics and eld theory. In the path integral version of this approximation, the paths giving the largest contribution to the Green function lie close to the \saddle-point" of the Euclidean action, called the instanton.

To describe the disordered Peierls chain we use the Fluctuating G ap M odel (FGM). It has previously been considered in the context of the therm odynam ical properties of quasi-one-dimensional organic compounds (NMP-TCNQ, TTF-TCNQ), and has been applied to study the elect of disorder on the Peierls transition, as well as the elect of quantum lattice uctuations on the optical spectrum of Peierls materials. In this model the electron motion is described by the one-dimensional Dirac equation,

$$\hat{h} = {}_{3}\frac{V_{F}}{i}\frac{d}{dx} + {}_{1}(x) (x) = "(x);$$
(1)

where $_{1}$ and $_{3}$ are the Paulim atrices and $_{0}$

$$(x) = \begin{bmatrix} B & R & (x) & C \\ B & & C \\ A & & A \end{bmatrix}$$

is the wave function of the single-electron state close to the Fermi energy $\P_F = 0$. The rst term in the Hamiltonian \hat{h} describes the free motion of the electrons and the two

am plitudes $_R$ (x) and $_L$ (x) correspond to particles m oving, respectively, to the right and to the left with the Ferm i velocity v_F . The second term in the H am iltonian describes the backward scattering of electrons from the lattice distortion wave, whose am plitude is proportional to (x). D isorder is modelled by assuming (x) to uctuate randomly along the chain around some average value $_0$,

$$(x) = {}_{0} + (x); \qquad (2)$$

where (x) is the uctuating part with a Gaussian correlator,

h (x) (y)
$$i = A$$
 (x y): (3)

In the absence of disorder ((x) = 0), the electron spectrum has a gap between the energies "= 0 and "= + 0. At nonzero disorder the average density of states lying close to the middle of the pseudogap (j"j 0) was found in Ref. 3 by means of the \phase form alism ", 12

h (")i/
$$7^{-\frac{2}{p}-1}$$
; (4)

where $g=A/(v_F_0)$. We note that due to the charge conjugation symmetry (particle-hole symmetry) of the D irac H am iltonian \hat{h} , the density of states is a symmetric function of the energy h (")i=h (")i, and in what follows we will assume " to be positive.

From Eq.(4) it is clear that at weak disorder (g 1) the density of states close to the middle of the pseudogap is strongly suppressed. As we mentioned above, the explanation for this is that a large uctuation of (x) is required in order to create an electron state with energy " 0. This motivates us to apply the \saddle-point" approach to study the typical electron states and to calculate disorder averages. The \saddle-point" disorder uctuation (or instanton) (x) is the least suppressed one among the required large uctuations. It can be found by minimizing,

A [(x)] =
$$\frac{1}{2A}$$
 dx ² (x) (", [(x)] "): (5)

The rst term in this equation describes the suppression of the probability of the uctuation with the correlator Eq. (3) (the weight p[(x)] of the disorder con guration is

exp $\frac{1}{2A}$ Rdx 2 (x)), while the second term stems from the condition that the energy $"_+$ [(x)] of the lowest positive energy single-electron state for the disorder realization (x) equals ". The factor is a Lagrange multiplier. The minimization of A [(x)] gives,

$$(x) = A + (x) + (x);$$
 (6)

where $_{+}$ (x) is the wave function of the state with energy $"_{+}$ [(x)].

It may be shown by inspection that the solution of Eq.(6) is a soliton-antisoliton pair con guration,

where x_0 describes the position of the disorder uctuation in the chain, R is the distance between the soliton and the antisoliton, and K is determined by

$$v_F K = 0 \tanh (K R)$$
: (8)

The instanton is shown in Fig. 1 by plotting $(x) = _0 + _0 (x)$. The spectrum of electron states that occur for this (x) has previously been considered $^{13;14}$ in relation with polarons in the Su-Schrie er-H eeger model of conjugated polymers, $^{15;16}$ and is depicted in Fig. 2. It consists of a valence band (with highest energy $_0$), a conduction band (with lowest energy $_0$), and two localized intragap states with energies 14 (R), where

$$"_{+} (R) = \frac{0}{\cosh(K R)} :$$
 (9)

Thus, the soliton-antisoliton separation R is xed by the condition $"_+$ (R) = ". The two intragap states are the bonding and antibonding superpositions of the m idgap states localized near the soliton and antisoliton:

$$R_{R}(\mathbf{x}) = R_{L}(\mathbf{x}) = \frac{s - 2}{\frac{K}{8} \cdot 4} \frac{e^{i\frac{\pi}{4}}}{\cosh K(\mathbf{x} + \mathbf{x}_{0} + \frac{R}{2})} - \frac{e^{i\frac{\pi}{4}}}{\cosh K(\mathbf{x} + \mathbf{x}_{0} + \frac{R}{2})} = \frac{3}{\cosh K(\mathbf{x} + \mathbf{x}_{$$

(y (x) is schem atically plotted in Fig.1). The energy splitting 2" decreases exponentially with the soliton-antisoliton separation, so that for " $_{0}$,

R
$$_{0} \ln \frac{2_{0}}{"};$$
 (11)

where $_0 = v_F = _0$ is the correlation length. The suppression factor Eq.(5),

A [(x)]
$$\frac{1}{2A} (2_0)^2 R = \frac{2}{g} \ln \frac{2_0}{"}$$
; (12)

also depends logarithm ically on energy, so that the weight of the saddle-point con guration is,

$$p[(x)]/ \frac{x^2}{g}$$
: (13)

This result already gives a good estimate for the shape of the density of states inside the pseudogap at g 1 (cf. Eq.(4)).

A more detailed calculation requires performing the Gaussian integration over the disorder realizations close to the \saddle-point" con guration Eq.(7). We then not the following expression for the average density of electron states per unit length,

h (")
$$i = \frac{e}{gv_F} \frac{e^m}{2_0} \frac{\frac{2}{g}}{1} :$$
 (14)

Forg 1, this agrees with Eq.(36) of Ref. 3, con rm ing the validity of the \saddle-point" approximation at small energies and weak disorder. The easiest way to get the result Eq.(14) is to use the correspondence between the averaging over disorder realizations (x) and the quantum -m echanical averaging over the ground state for a certain double-well potential. The details of the calculation will be reported elsewhere.

Having obtained the form of the most probable disorder-induced electron states, we can now also calculate in a relatively straightforward way the optical absorption coefcient for a half-lled chain at photon energy! 2 $_0$ and g 1. Again, only a large disorder uctuation can make the energy dierence between the empty and lled electron levels small. With the highest probability the photon absorption will induce a transition from the highest occupied to the lowest unoccupied electron state. Due to the particle-hole symmetry, the energy of the lowest unoccupied state at half-lling should equal +1=2, while the energy of the highest doubly occupied state should equal +1=2.

Hence, the \saddle-point" disorder con guration, whose probability largely determ ines the absorption rate, is given by Eqs.(7), (8), and (9) with $"_+$ (R) = !=2.

Thus, in the \saddle-point" approximation, the absorption coe cient is the product of the averaged density of states (which is essentially the probability to not the necessary disorder uctuation) and the strength of the optical transition between the two intragap levels:

h (!)
$$i = hC!$$
 hf $\hat{g}i\hat{D}i^2$ (E_f E₀ !) $i \frac{C!}{2}$ h+ $\hat{g}i\hat{j}$ i^2 h (" = !=2) i : (15)

Here \hat{d} is the electric dipole operator, j idenote the wave functions of the intragap states (with energies !=2) and C is an !-independent coe cient (for small!, we can neglect the weak!-dependence of the real part of the dielectric constant).

The wave functions of the intragap states j i are the bonding and antibonding superpositions of the wave functions of the midgap states localized near the soliton and the antisoliton (see Eq.(10)), from which the transition dipole matrix element is obtained as,

$$h + j\hat{\mathbf{d}}j \quad i = \frac{q\mathbf{R}}{2} : \tag{16}$$

Here q denotes the electron charge and R is the soliton-antisoliton separation. Thus, for the asymptotic behavior of the averaged absorption coe cient at low photon energy we obtain,

h (!)i/!
$$\frac{2}{g}$$
 ln $\frac{4}{1}$: (17)

At this point we want to comment on the calculations of the optical conductivity in Refs. 9 and 11, in which the factorization approximation, hGGi = hGihGi, was used to evaluate the disorder average of the product of two Green functions. From above, it is clear that this approximation is not valid at low photon energies, as it results in the optical conductivity (as well as the absorption coe cient) being proportional to the second power of the weight Eq.(13), rather than the rst (cf. Eq.(15)). Of course, at weak disorder the absorption at photon energies! 2 $_0$ is small anyhow, but the factorization approximation makes it even much smaller.

We would also like to point out that the small dierence between the energies of the bonding and antibonding states is potentially dangerous for the saddle-point calculation of both the average optical absorption coecient and density of states. The problem arises in the calculation of the contribution of the disorder realizations close to the \saddle-point" uctuation:

$$(x) = (x) + (x)$$
:

The perturbation $\hat{h} = \frac{1}{1}$ (x) can, in principle, strongly m ix the bonding and antibonding states, because of the small energy denominator 2" appearing in the perturbation series. Such mixing would a ect the values of both the energy splitting between the two states and the dipole matrix element. To see if that is the case, we considered the elective perturbation H amiltonian, acting on the subspace of the two bonding and antibonding states, which includes the virtual excitations to all other (high-energy) electron states. We found that the ordiagonal matrix elements of this H amiltonian are O ("), which cancels "in the denominator and makes the mixing of the two states small. This result is a direct consequence of the charge conjugation symmetry of the Dirac H amiltonian Eq.(1). Thus, despite the small energy splitting, the saddle-point method is applicable.

We conclude that in the FGM the most probable form of the wave function of the electron state lying deep within the pseudogap contains two peaks. The \saddle-point" disorder uctuation, which induces such a state, has the form of a soliton-antisoliton pair and the peaks of the wave function are localized near the two kinks of this uctuation (see Fig. 1). Away from the kinks, the electron wave function Eq.(10) falls o exponentially on a length scale $_{0}$. This observation is consistent with the fact, that the localization length at zero energy,

$$l_{loc}(" = 0) = \frac{0}{(1 - \frac{g}{2})};$$

calculated using the Thouless form ula_1^{17} at weak disorder equals the correlation length 0. As we demonstrated, the instanton approach allows for a relatively easy calculation of the small-energy density of states and absorption coe cient.

Our results (Eqs.(14) and Eq.(17)) are valid if the density of the disorder-induced states is small, which is the case when j''j $_{\scriptscriptstyle 0}$ and ${\sf g}$ 1. It is useful, however, to com m ent brie y on e ects of large disorder. For g 1 the typical size of the disorder uctuation (x) on a scale of the correlation length $_0$ becomes comparable to $_0$, so that disorder uctuations inducing the electron states with small energy are no longer suppressed, and for q > 2 the density of states even diverges at " = 0.3 This is essentially the singularity found long ago by Dyson¹⁸ for a gapless system, because at strong disorder there is no principal di erence between the electron states in Peierls insulators and conducting ($_0 = 0$) chains. In the latter case the localization length of the electron states diverges as "! 0 and the wave functions have an irregular structure, being large in m any separated chain regions. ¹⁹ Surprisingly, the \saddle-point" m ethod gives the correct exponent (2=g 1) (cf. Eq.(14)) for the energy dependence of the average density of states at all values of g. This suggests, that even at large g the typical form of the wave function m ay be close to the one given by Eq.(10) in the regions where the wave function is large, and that multi-instanton disorder con gurations (a gas of the soliton-antisoliton pairs) m ay becom e im portant at strong disorder.

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FIGURE CAPTIONS

- FIG.1. The form of $(x) = _0 + (x)$ for the instanton disorder uctuation (thick line) and the electron density $j_+(x)j_-^2 = j_-(x)j_-^2$ for the corresponding intragap states (dotted line).
- FIG. 2. The spectrum of electron states for the instanton con guration (x) plotted in Fig. 1.

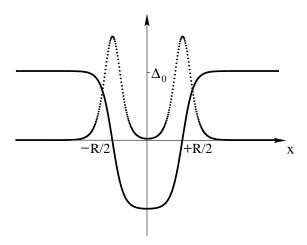


FIG.1

